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PHASE CONTROL THYRISTOR AT720HT

Repetitive voltage up to 1400 v

Mean on-state current 3950 A

Surge current 60 kA

TARGET SPECIFICATION

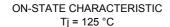
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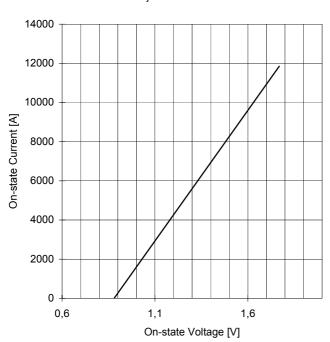
Symbol	Characteristic	Conditions	Tj [°C]	Value	Unit
BLOCK	ING				
V RRM	Repetitive peak reverse voltage		125	1400	V
V RSM	Non-repetitive peak reverse voltage		125	1500	V
V DRM	Repetitive peak off-state voltage		125	1400	V
I RRM	Repetitive peak reverse current	V=VRRM	125	200	mA
I DRM	Repetitive peak off-state current	V=VDRM	125	200	mA
CONDU	ICTING				
I T (AV)	Mean on-state current	180° sin, 50 Hz, Th=55°C, double side cooled		3950	Α
I T (AV)	Mean on-state current	180° sin, 50 Hz, Tc=85°C, double side cooled		3070	Α
I TSM	Surge on-state current	sine wave, 10 ms	125	60	kA
l² t	l² t	without reverse voltage		18000 x1E3	A²s
Vт	On-state voltage	On-state current = 4000 A	125	1,18	V
V T(TO)	Threshold voltage		125	0,88	V
rт	On-state slope resistance		125	0,075	mohm
SWITCH	HING	•			
di/dt	Critical rate of rise of on-state current, min.	From 75% VDRM up to 3000 A, gate 10V 50hm	125	200	A/µs
dv/dt	Critical rate of rise of off-state voltage, min.	Linear ramp up to 75% of VDRM	125	1000	V/µs
td	Gate controlled delay time, typical	VD=100V, gate source 25V, 10 ohm , tr=.5 μs	25	3	μs
tq	Circuit commutated turn-off time, typical	dV/dt = 20 V/µs linear up to 80% VDRM		320	μs
Q rr	Reverse recovery charge	di/dt=-20 A/μs, I= 2000 A	125		μC
l rr	Peak reverse recovery current	VR= 50 V			Α
Iн	Holding current, typical	VD=5V, gate open circuit	25	300	mA
Īι	Latching current, typical	VD=5V, tp=30µs	25	700	mA
GATE				l .	
V gt	Gate trigger voltage	VD=5V	25	3,5	V
I GT	Gate trigger current	VD=5V	25	350	mA
V GD	Non-trigger gate voltage, min.	VD=VDRM	125	0,25	V
V FGM	Peak gate voltage (forward)			30	V
l FGM	Peak gate current			10	Α
V RGM	Peak gate voltage (reverse)			5	V
P GM	Peak gate power dissipation	Pulse width 100 μs		150	W
P G	Average gate power dissipation	·		2	W
MOUNT	· · · · · · · · · · · · · · · · · · ·				
R th(j-h)	Thermal impedance, DC	Junction to heatsink, double side cooled		11,0	°C/kW
R th(c-h)	Thermal impedance	Case to heatsink, double side cooled		2	°C/kW
T j	Operating junction temperature	222.0 0.00.00		-30 / 125	°C
F	Mounting force			46.0 / 54.0	kN
	Mass			1500	g

AT720HT PHASE CONTROL THYRISTOR

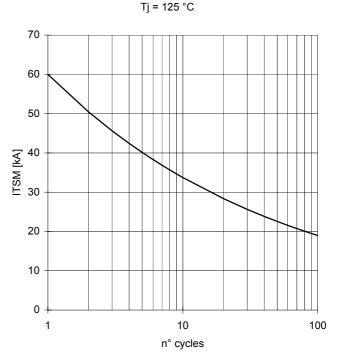


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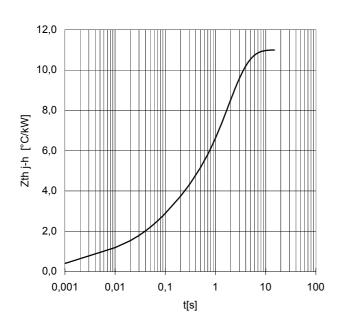




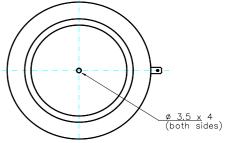
SURGE CHARACTERISTIC



TRANSIENT THERMAL IMPEDANCE DOUBLE SIDE COOLED



Ø 101 Ø 73 Ø 110 max





Cathode terminal type DIN 46244 - A 4.8 - 0.8 Gate terminal type AMP 60598 - 1

All the characteristics given in this data sheet are guaranteed only with uniform clamping force, cleaned and lubricated heatsink, surfaces with flatness < .03 mm and roughness < 2 μ m.

In the interest of product improvement POSEICO SPA reserves the right to change any data given in this data sheet at any time without previous notice.

If not stated otherwise the maximum value of ratings (simbols over shaded background) and characteristics is reported.

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